3207A
QUAD BIPOLAR-TO-MOS LEVEL SHIFTER AND DRIVER

- **High Speed, 45 nsec Max. — Delay + Transition Time Over Temperature with 200 pF Load**
- **TTL and DTL Compatible Inputs**
- **1103 and 1103A Memory Compatible at Output**
- **Simplifies Design — Replaces Discrete Components**
- **Easy to Use — Operates from Standard Bipolar and MOS Supplies**
- **Minimum Line Reflection — Input and Output Clamp Diodes**
- **High Input Breakdown Voltage — 19 Volts**
- **CerDIP Package — 16 Pin DIP**

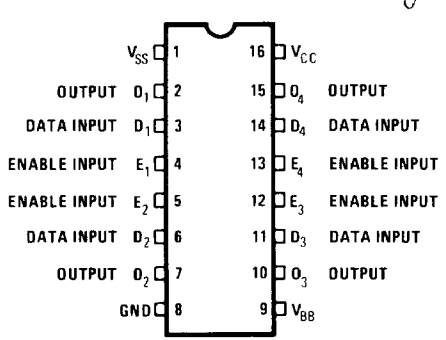
The 3207A is a Quad Bipolar-to-MOS level shifter and driver which accepts TTL and DTL input signals, and provides high output current and voltage suitable for driving MOS circuits. It is particularly suitable for driving the 1103 and 1103A memory chips. The circuit operates from a 5 volt TTL power supply, and V_{SS} and V_{BB} power supplies from the 1103 and 1103A.

The device features two common enable inputs per pair of devices which permits some logic to be done at their inputs, such as cenable and precharge decoding for the 1103 and 1103A.

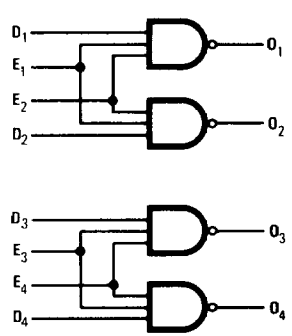
For the TTL inputs a logic "1" is V_{IH} and a logic "0" is V_{IL}. The 3207A outputs correspond to a logic "1" as V_{OL} and a logic "0" as V_{OH} for driving MOS inputs.

The 3207A is packaged in a hermetically sealed 16 pin ceramic dual-in-line package. The device performance is specified over the same temperature range as the 1103 and 1103A, i.e. from 0°C to +70°C.

PIN CONFIGURATION



LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias ..... 0°C to +70°C
Storage Temperature..... −65°C to +160°C
All Input Voltages and V_{SS}..... −1.0 to +21V
Supply Voltage V_{CC} ..... −1.0 to +7V
All Outputs and Supply Voltage
V_{BB} with respect to GND ..... −1.0 to +25V
Power Dissipation at 25°C..... 2 Watts (1)

*COMMENT
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

(1) Refer to the graph of Junction Temperature versus Total Power Dissipation on page 5-10 for other temperatures.

D.C. CHARACTERISTICS $T_A = 0°C$ to $70°C$, $V_{CC} = 5V \pm 5\%$, $V_{SS} = 16V \pm 5\%$, $V_{BB} - V_{SS} = 3.0V$ to $4.0V$

SYMBOL	TEST	LIMIT MIN.	LIMIT MAX.	UNIT	CONDITIONS
I_{FD}	DATA INPUT LOAD CURRENT		−0.25	mA	$V_D = .45V$, $V_{CC} = 5.25V$, All Other Inputs at 5.25V, $V_{SS} = 16V$, $V_{BB} = 19V$
I_{FE}	ENABLE INPUT LOAD CURRENT		−0.50	mA	$V_E = .45V$, $V_{CC} = 5.25V$, All Other Inputs at 5.25V, $V_{SS} = 16V$, $V_{BB} = 19V$
I_{RD}	DATA INPUT LEAKAGE CURRENT		20	μA	$V_D = 19V$, $V_{CC} = 5.0V$, All Other Inputs Grounded, $V_{SS} = 16V$, $V_{BB} = 19V$
I_{RE}	ENABLE INPUT LEAKAGE CURRENT		20	μA	$V_E = 19V$, $V_{CC} = 5.0V$, All Other Inputs Grounded, $V_{SS} = 16V$, $V_{BB} = 19V$
V_{OL}	OUTPUT "LOW" VOLTAGE		.8 .7 .6	V(0°C) V(25°C) V(70°C)	$I_{OL} = 500\mu A$, $V_{CC} = 4.75V$ $V_{SS} = 16V$, $V_{BB} = 19V$ All Inputs at 2.0V
V_{OH} (MIN.)	OUTPUT "HIGH" VOLTAGE	$V_{SS} - .7$ $V_{SS} - .6$ $V_{SS} - .5$		V(0°C) V(25°C) V(70°C)	$I_{OH} = -500\mu A$, $V_{CC} = 5.0V$ $V_{SS} = 16V$, $V_{BB} = 19V$ All Inputs at 0.85V
V_{OH} (MAX.)			$V_{SS} + 1.0$	V	$I_{OH} = 5mA$, $V_{CC} = 5.0V$ $V_{SS} = 16V$, $V_{BB} = 19V$
I_{OL}	OUTPUT SINK CURRENT	100		mA	$V_O = 4V$, $V_{CC} = 5.0V$, $V_{SS} = 16V$, $V_{BB} = 19V$, $V_E = V_D = 2.0V$
I_{OH}	OUTPUT SOURCE CURRENT	−100		mA	$V_O = V_{SS} - 4V$, $V_{CC} = 5.0V$, $V_{SS} = 16V$ $V_{BB} = 19V$, $V_E = V_D = 0.85V$
V_{IL}	INPUT "LOW" VOLTAGE		1.0	V	$V_{CC} = 5.0V$, $V_{SS} = 16V$, $V_{BB} = 19V$
V_{IH}	INPUT "HIGH" VOLTAGE	2.0		V	$V_{CC} = 5.0V$, $V_{SS} = 16V$, $V_{BB} = 19V$
C_{IN}	INPUT CAPACITANCE	8(Typical)		pF	$V_{BIAS} = 2.0V$, $V_{CC} = 0V$

POWER SUPPLY CURRENT DRAIN:

All Outputs "Low"

Symbol	Parameter	Min.	Max.	Unit	Conditions
I_{CC}	Current from V_{CC}		83	mA	$V_{CC} = 5.25V$, $V_{SS} = 16.8V$, $V_{BB} = 20.8V$ All Inputs Open
I_{SS}	Current from V_{SS}		250	μA	
I_{BB}	Current from V_{BB}		21	mA	
P_{TOTAL}	Total Power Dissipation		900	mW	

All Outputs "High"

I_{CC}	Current from V_{CC}		33	mA	$V_{CC} = 5.25V$, $V_{SS} = 16.8V$, $V_{BB} = 20.8V$ All Inputs Grounded
I_{SS}	Current from V_{SS}		250	μA	
I_{BB}	Current from V_{BB}		3	mA	
P_{TOTAL}	Total Power Dissipation		250	mW	

Standby Condition with $V_{CC} = 0V$, $V_{SS} = V_{BB}$

I_{CC}	Current from V_{CC}		0	mA	$V_{CC} = 0V$, $V_{SS} = 16.8V$, $V_{BB} = 16.8V$
I_{SS}	Current from V_{SS}		250	μA	
I_{BB}	Current from V_{BB}		250	μA	
P_{TOTAL}	Total Power Dissipation		10	mW	

SWITCHING CHARACTERISTICS

A.C. CHARACTERISTICS

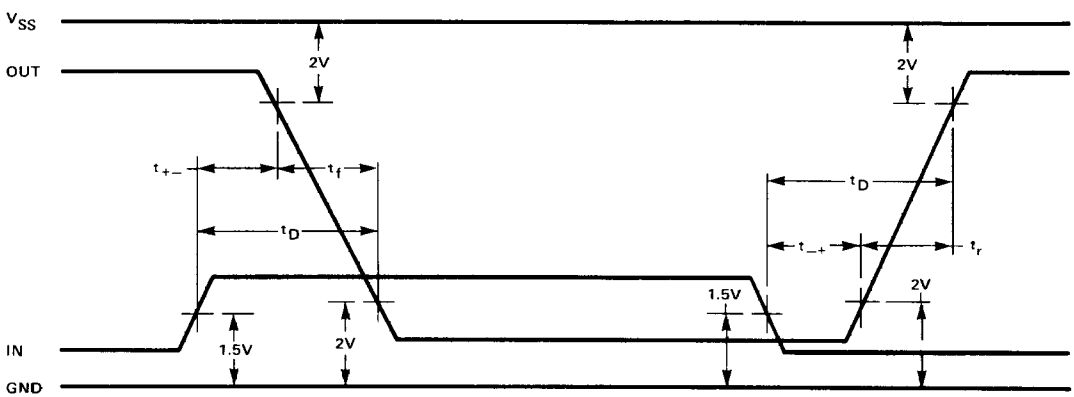
T_A = 0°C to 70°C, V_{CC} = 5V ±5%, V_{SS} = 16V ±5%, V_{BB} = V_{SS} +3 to 4V, f = 2 MHz, 50% Duty Cycle

SYMBOL	TEST	LIMITS (ns)				
		C_L = 100 pF		C_L = 200 pF		DELAY DIFFERENTIAL (1) C_L = 200 pF
		MIN.	MAX.	MIN.	MAX.	MAX.
t_{+-}	INPUT TO OUTPUT DELAY	5	15	5	15	5
t_{-+}	INPUT TO OUTPUT DELAY	5	25	5	25	10
t_r	OUTPUT RISE TIME	5	20	5	30	10
t_f	OUTPUT FALL TIME	5	20	10	30	10
t_D	DELAY + RISE OR FALL TIME	10	35	20	45	10

(1) This is defined as the maximum skew between any output in the same package, eg., all the input to output delays for the t_{-+} parameter are within a maximum of 10 nsec of each other in the same package.

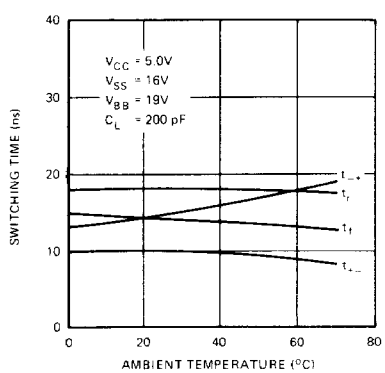
MEMORY SUPPORT

WAVEFORMS

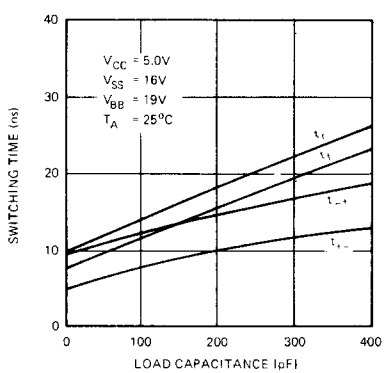


TYPICAL CHARACTERISTICS

SWITCHING TIME VS. AMBIENT TEMPERATURE

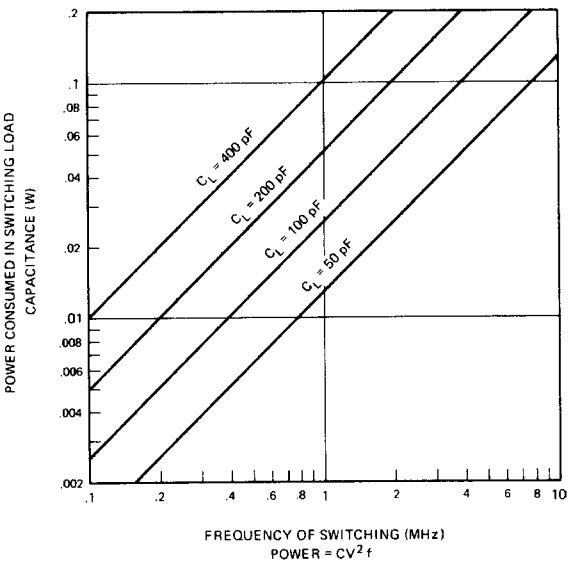


SWITCHING TIME VS. LOAD CAPACITANCE

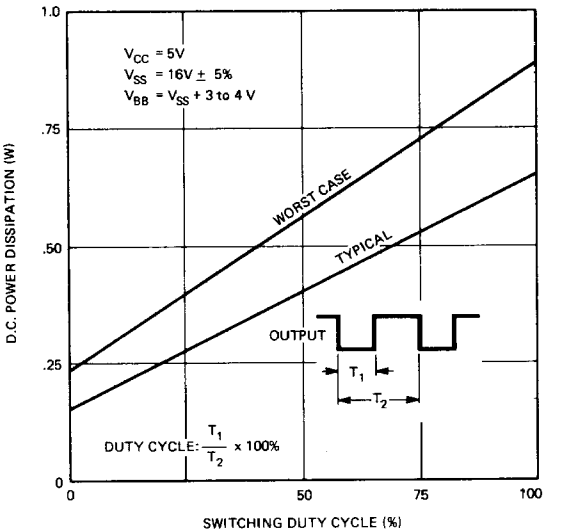


POWER AND SWITCHING CHARACTERISTICS

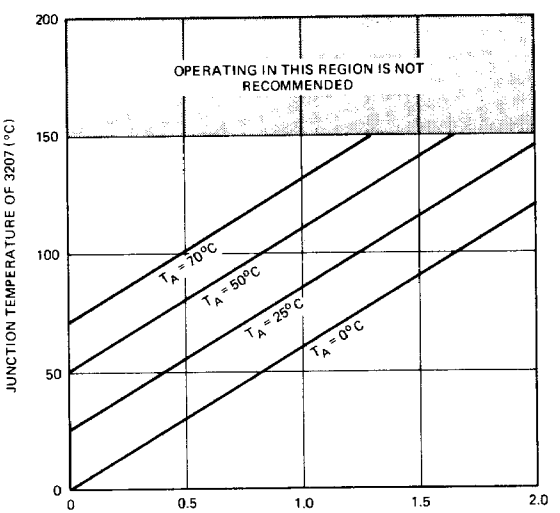
POWER CONSUMED IN CHARGING AND DISCHARGING LOAD CAPACITANCE OVER 0V TO 16V INTERVAL



NO LOAD D.C. POWER DISSIPATION VS. OPERATING DUTY CYCLE



JUNCTION TEMPERATURE VS. TOTAL POWER DISSIPATION OF THE CIRCUIT



WORST CASELOAD CAPACITANCE ON EACH OUTPUT VS. FREQUENCY OF SWITCHING